Amendment to the Claims

This listing of claims will replace all prior versions and listings of claims in the application.

Listing of Claims

1. – 5. (Canceled)

6. (Previously Presented) A semiconductor device comprising an oxide-nitride gate dielectric having substantially equal gate to substrate capacitance as an oxide gate dielectric comprising a thickness less than approximately 20 angstroms, wherein the oxide-nitride gate dielectric comprises:

a silicon dioxide layer and a distinct silicon nitride layer; and

a thickness that varies by less than approximately 5% across the semiconductor topography.

7. (Previously Presented) The semiconductor device of claim 6, wherein said oxide-nitride gate dielectric has a substantially equal gate to substrate capacitance as an oxide gate dielectric having a thickness between approximately 10 angstroms and approximately 15 angstroms.

8. (Previously Presented) The semiconductor device of claim 6, wherein said silicon dioxide layer comprises a thickness between approximately 6 angstroms and approximately 10 angstroms, and wherein said distinct silicon nitride layer comprises a thickness between approximately 15 angstroms and approximately 20 angstroms.

9. – 18. (Canceled)

19. (Previously Presented) A method for forming an oxide-nitride stack upon a semiconductor topography, comprising:

growing an oxide film upon the semiconductor topography in a first chamber at a first temperature, wherein said growing comprises rinsing the semiconductor topography with an ozonated substance;

transferring the semiconductor topography from said first chamber to a second chamber, wherein said transferring comprises exposing the semiconductor topography to a substantially equal temperature as said first temperature;

forming a nitride layer upon the oxide film in said second chamber at a second temperature; and

forming a second oxide film upon and in contact with the nitride film at a fourth temperature, wherein said fourth temperature is greater than the first temperature.

20. (Original) The method of claim 19, wherein said first temperature is between approximately 10 °C and approximately 30 °C.

21. (Original) The method of claim 19, wherein said second temperature is between approximately 750 °C and approximately 800 °C.

22. (Canceled)

23. (Original) The method of claim 19, further comprising annealing said semiconductor topography at a third temperature subsequent to said forming the nitride layer.

24. (Original) The method of claim 23, wherein said third temperature is between approximately 750 °C and approximately 850 °C.

25. – 35. (Canceled)